2SA1890

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SC5026

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- High collector-emitter voltage (Base open) V_{CEO}
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-80	V
Collector-emitter voltage (Base open)	V _{CEO}	-80	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	Ic	-1	A
Peak collector current	I_{CP}	-1.5	A
Collector power dissipation *	P _C	1	W
Junction temperature	T_{j}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu \text{A}, I_{\rm E} = 0$	-80			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = \bigcap mA$, $I_B = 0$	-80			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm P} = -10 \mu A, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -40 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio	hFE 1*2	$V_{CE} = -2 \text{ V}, I_{C} = -100 \text{ mA}$	120		340	_
	h _{FE2} *1	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	60			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.3	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		15	30	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	R	S
h _{FE1}	120 to 240	170 to 340

Unit: mm

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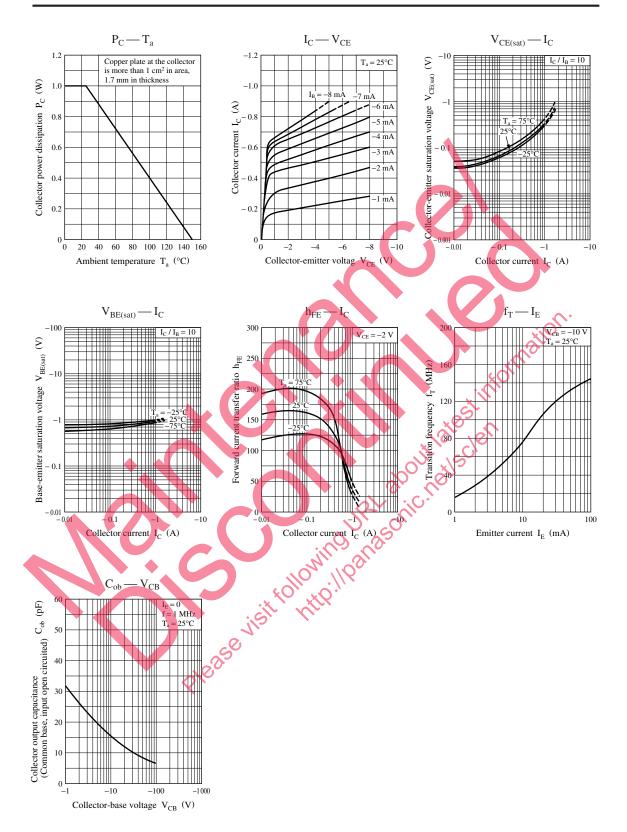
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